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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "<u>Embedded -</u> <u>Microcontrollers</u>"

Details

Product Status	Active
Core Processor	ARM® Cortex®-M4
Core Size	32-Bit Single-Core
Speed	100MHz
Connectivity	CANbus, EBI/EMI, I ² C, IrDA, SD, SPI, UART/USART
Peripherals	DMA, I ² S, LVD, POR, PWM, WDT
Number of I/O	90
Program Memory Size	512KB (512K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	128K x 8
Voltage - Supply (Vcc/Vdd)	1.71V ~ 3.6V
Data Converters	A/D 42x16b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	121-LFBGA
Supplier Device Package	121-MAPBGA (8x8)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/mk10dn512vmc10

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

Terminology and guidelines

Field	Description	Values
FFF	Program flash memory size	 32 = 32 KB 64 = 64 KB 128 = 128 KB 256 = 256 KB 512 = 512 KB 1M0 = 1 MB
R	Silicon revision	 Z = Initial (Blank) = Main A = Revision after main
Т	Temperature range (°C)	 V = -40 to 105 C = -40 to 85
PP	Package identifier	 FM = 32 QFN (5 mm x 5 mm) FT = 48 QFN (7 mm x 7 mm) LF = 48 LQFP (7 mm x 7 mm) LH = 64 LQFP (10 mm x 10 mm) MP = 64 MAPBGA (5 mm x 5 mm) LK = 80 LQFP (12 mm x 12 mm) LL = 100 LQFP (14 mm x 14 mm) MC = 121 MAPBGA (8 mm x 8 mm) LQ = 144 LQFP (20 mm x 20 mm) MD = 144 MAPBGA (13 mm x 13 mm) MJ = 256 MAPBGA (17 mm x 17 mm)
СС	Maximum CPU frequency (MHz)	 5 = 50 MHz 7 = 72 MHz 10 = 100 MHz 12 = 120 MHz 15 = 150 MHz
N	Packaging type	 R = Tape and reel (Blank) = Trays

2.4 Example

This is an example part number:

MK10DN512ZVMD10

3 Terminology and guidelines

3.1 Definition: Operating requirement

An *operating requirement* is a specified value or range of values for a technical characteristic that you must guarantee during operation to avoid incorrect operation and possibly decreasing the useful life of the chip.

3.1.1 Example

This is an example of an operating requirement, which you must meet for the accompanying operating behaviors to be guaranteed:

Symbol	Description	Min.	Max.	Unit
V _{DD}	1.0 V core supply voltage	0.9	1.1	V

3.2 Definition: Operating behavior

An *operating behavior* is a specified value or range of values for a technical characteristic that are guaranteed during operation if you meet the operating requirements and any other specified conditions.

3.2.1 Example

This is an example of an operating behavior, which is guaranteed if you meet the accompanying operating requirements:

Symbol	Description	Min.	Max.	Unit
I _{WP}	Digital I/O weak pullup/ pulldown current	10	130	μA

3.3 Definition: Attribute

An *attribute* is a specified value or range of values for a technical characteristic that are guaranteed, regardless of whether you meet the operating requirements.

3.3.1 Example

This is an example of an attribute:

Symbol	Description	Min.	Max.	Unit
CIN_D	Input capacitance: digital pins	_	7	pF

3.8.1 Example 1

This is an example of an operating behavior that includes a typical value:

Symbol	Description	Min.	Тур.	Max.	Unit
I _{WP}	Digital I/O weak pullup/pulldown current	10	70	130	μΑ

3.8.2 Example 2

This is an example of a chart that shows typical values for various voltage and temperature conditions:



3.9 Typical value conditions

Typical values assume you meet the following conditions (or other conditions as specified):

Symbol	Description	Value	Unit
T _A	Ambient temperature	25	٥C
V _{DD}	3.3 V supply voltage	3.3	V

Symbol	Description	Min.	Max.	Unit	Notes
t _{POR}	After a POR event, amount of time from the point V_{DD} reaches 1.71 V to execution of the first instruction across the operating temperature range of the chip.	_	300	μs	1
	• VLLS1 → RUN	_	112	μs	
	VLLS2 → RUN	_	74	μs	
	• VLLS3 → RUN	_	73	μs	
	• LLS → RUN	_	5.9	μs	
	VLPS → RUN	_	5.8	μs	
	• STOP → RUN	_	5	μs	

Table 5. Power mode transition operating behaviors

1. Normal boot (FTFL_OPT[LPBOOT]=1)

5.2.5 Power consumption operating behaviors Table 6. Power consumption operating behaviors

Symbol	Description	Min.	Тур.	Max.	Unit	Notes
I _{DDA}	Analog supply current	—	—	See note	mA	1
I _{DD_RUN}	Run mode current — all peripheral clocks disabled, code executing from flash • @ 1.8V • @ 3.0V		37 38	63 64	mA mA	2
I _{DD_RUN}	Run mode current — all peripheral clocks enabled, code executing from flash • @ 1.8V • @ 3.0V • @ 25°C • @ 125°C		46 47 58	77 63 79	mA mA mA	3, 4
I _{DD_WAIT}	Wait mode high frequency current at 3.0 V — all peripheral clocks disabled		20	_	mA	2
I _{DD_WAIT}	Wait mode reduced frequency current at 3.0 V — all peripheral clocks disabled		9		mA	5
I _{DD_VLPR}	Very-low-power run mode current at 3.0 V — all peripheral clocks disabled	_	1.12	—	mA	6
I _{DD_VLPR}	Very-low-power run mode current at 3.0 V — all peripheral clocks enabled		1.71	_	mA	7

Table continues on the next page ...

General

3. Specified according to Annex D of IEC Standard 61967-2, Measurement of Radiated Emissions – TEM Cell and Wideband TEM Cell Method

5.2.7 Designing with radiated emissions in mind

To find application notes that provide guidance on designing your system to minimize interference from radiated emissions:

- 1. Go to www.freescale.com.
- 2. Perform a keyword search for "EMC design."

5.2.8 Capacitance attributes

Table 8. Capacitance attributes

Symbol	Description	Min.	Max.	Unit
C _{IN_A}	Input capacitance: analog pins	—	7	pF
C _{IN_D}	Input capacitance: digital pins	—	7	pF

5.3 Switching specifications

5.3.1 Device clock specifications

Table 9. Device clock specifications

Symbol	Description	Min.	Max.	Unit	Notes		
	Normal run mode						
f _{SYS}	System and core clock	_	100	MHz			
f _{BUS}	Bus clock	—	50	MHz			
FB_CLK	FlexBus clock	—	50	MHz			
f _{FLASH}	Flash clock	—	25	MHz			
f _{LPTMR}	LPTMR clock	—	25	MHz			
	VLPR mode ¹						
f _{SYS}	System and core clock	—	4	MHz			
f _{BUS}	Bus clock	—	4	MHz			
FB_CLK	FlexBus clock	—	4	MHz			
f _{FLASH}	Flash clock	—	0.5	MHz			
f _{ERCLK}	External reference clock	—	16	MHz			
f _{LPTMR_pin}	LPTMR clock	_	25	MHz			
f _{LPTMR_ERCLK}	LPTMR external reference clock		16	MHz			

Board type	Symbol	Description	121 MAPBGA	Unit	Notes
	Ψ _{JT}	Thermal characterization parameter, junction to package top outside center (natural convection)	3	°C/W	4

- 1. Determined according to JEDEC Standard JESD51-2, Integrated Circuits Thermal Test Method Environmental Conditions—Natural Convection (Still Air), or EIA/JEDEC Standard JESD51-6, Integrated Circuit Thermal Test Method Environmental Conditions—Forced Convection (Moving Air).
- 2. Determined according to JEDEC Standard JESD51-8, Integrated Circuit Thermal Test Method Environmental Conditions—Junction-to-Board.
- 3. Determined according to Method 1012.1 of MIL-STD 883, *Test Method Standard, Microcircuits*, with the cold plate temperature used for the case temperature. The value includes the thermal resistance of the interface material between the top of the package and the cold plate.
- 4. Determined according to JEDEC Standard JESD51-2, Integrated Circuits Thermal Test Method Environmental Conditions Natural Convection (Still Air).

6 Peripheral operating requirements and behaviors

6.1 Core modules

6.1.1 Debug trace timing specifications

Table 12. Debug trace operating behaviors

Symbol	Description	Min.	Max.	Unit
T _{cyc}	Clock period	Frequency	dependent	MHz
T _{wi}	Low pulse width	2	—	ns
T _{wh}	High pulse width	2	—	ns
T _r	Clock and data rise time	—	3	ns
T _f	Clock and data fall time	—	3	ns
Ts	Data setup	3	—	ns
T _h	Data hold	2	—	ns



Figure 3. TRACE_CLKOUT specifications



Figure 4. Trace data specifications

6.1.2 JTAG electricals

Table 13.	JTAG limited	voltage range	electricals
		vonage range	cicotiiouis

Symbol	Description	Min.	Max.	Unit
	Operating voltage	2.7	3.6	V
J1	TCLK frequency of operation			MHz
	Boundary Scan	0	10	
	JTAG and CJTAG	0	25	
	Serial Wire Debug	0	50	
J2	TCLK cycle period	1/J1	_	ns
J3	TCLK clock pulse width			
	Boundary Scan	50	_	ns
	JTAG and CJTAG	20	_	ns
	Serial Wire Debug	10	_	ns
J4	TCLK rise and fall times	_	3	ns
J5	Boundary scan input data setup time to TCLK rise	20	—	ns
J6	Boundary scan input data hold time after TCLK rise	0	_	ns
J7	TCLK low to boundary scan output data valid	—	25	ns
J8	TCLK low to boundary scan output high-Z	—	25	ns
J9	TMS, TDI input data setup time to TCLK rise	8	—	ns
J10	TMS, TDI input data hold time after TCLK rise	1	—	ns
J11	TCLK low to TDO data valid	—	17	ns
J12	TCLK low to TDO high-Z	—	17	ns
J13	TRST assert time	100		ns
J14	TRST setup time (negation) to TCLK high	8		ns

Table 14. JTAG full voltage range electricals

Symbol	Description	Min.	Max.	Unit
	Operating voltage	1.71	3.6	V

Symbol	Description	Min.	Max.	Unit
J1	TCLK frequency of operation			MHz
	Boundary Scan	0	10	
	JTAG and CJTAG	0	20	
	Serial Wire Debug	0	40	
J2	TCLK cycle period	1/J1		ns
J3	TCLK clock pulse width			
	Boundary Scan	50		ns
	JTAG and CJTAG	25	_	ns
	Serial Wire Debug	12.5	_	ns
J4	TCLK rise and fall times	—	3	ns
J5	Boundary scan input data setup time to TCLK rise	20		ns
J6	Boundary scan input data hold time after TCLK rise	0		ns
J7	TCLK low to boundary scan output data valid	—	25	ns
J8	TCLK low to boundary scan output high-Z	—	25	ns
J9	TMS, TDI input data setup time to TCLK rise	8		ns
J10	TMS, TDI input data hold time after TCLK rise	1.4		ns
J11	TCLK low to TDO data valid	—	22.1	ns
J12	TCLK low to TDO high-Z	—	22.1	ns
J13	TRST assert time	100	—	ns
J14	TRST setup time (negation) to TCLK high	8		ns

Table 14. JTAG full voltage range electricals (continued)



Figure 5. Test clock input timing





6.2 System modules

There are no specifications necessary for the device's system modules.

6.3 Clock modules

6.3.1 MCG specifications

Symbol	Description	Min.	Тур.	Max.	Unit	Notes
f _{ints_ft}	Internal reference frequency (slow clock) — factory trimmed at nominal VDD and 25 °C	_	32.768	—	kHz	
f _{ints_t}	Internal reference frequency (slow clock) — user trimmed	31.25	_	39.0625	kHz	
$\Delta_{fdco_res_t}$	Resolution of trimmed average DCO output frequency at fixed voltage and temperature — using SCTRIM and SCFTRIM	_	± 0.3	± 0.6	%f _{dco}	1
$\Delta f_{dco_res_t}$	Resolution of trimmed average DCO output frequency at fixed voltage and temperature — using SCTRIM only	_	± 0.2	± 0.5	%f _{dco}	1
Δf _{dco_t}	Total deviation of trimmed average DCO output frequency over voltage and temperature	_	+0.5/-0.7	± 3	%f _{dco}	1
Δf _{dco_t}	Total deviation of trimmed average DCO output frequency over fixed voltage and temperature range of 0–70°C	_	± 0.3	± 3	%f _{dco}	1
f _{intf_ft}	Internal reference frequency (fast clock) — factory trimmed at nominal VDD and 25°C		4	_	MHz	
f _{intf_t}	Internal reference frequency (fast clock) — user trimmed at nominal VDD and 25 °C	3	_	5	MHz	
f _{loc_low}	Loss of external clock minimum frequency — RANGE = 00	(3/5) x f _{ints_t}			kHz	
f _{loc_high}	Loss of external clock minimum frequency — RANGE = 01, 10, or 11	(16/5) x f _{ints_t}			kHz	

Table 15. MCG specifications

Table continues on the next page ...

Symbol	Description		Min.	Тур.	Max.	Unit	Notes
		F	LL				
f _{fll_ref}	FLL reference frec	quency range	31.25	—	39.0625	kHz	
f _{dco}	DCO output frequency range	Low range (DRS=00) 640 × f _{fll_ref}	20	20.97	25	MHz	2, 3
		Mid range (DRS=01) 1280 × f _{fll ref}	40	41.94	50	MHz	
		Mid-high range (DRS=10) 1920 $\times f_{fill ref}$	60	62.91	75	MHz	-
		High range (DRS=11) 2560 × f _{fll ref}	80	83.89	100	MHz	-
f _{dco_t_DMX32}	DCO output frequency	Low range (DRS=00) 732 × f _{fll_ref}	-	23.99	—	MHz	4, 5
		Mid range (DRS=01) 1464 × f _{fll_ref}	_	47.97	_	MHz	
		Mid-high range (DRS=10) 2197 × f _{fll_ref}	_	71.99	_	MHz	
		High range (DRS=11) 2929 × f _{fll_ref}	_	95.98	_	MHz	
J _{cyc_fll}	FLL period jitter		_	180	_	ps	
	 f_{VCO} = 48 M f_{VCO} = 98 M 	Hz Hz	_	150	_		
t _{fll_acquire}	FLL target frequer	ncy acquisition time	—	—	1	ms	6
	1	Р	LL		1		I
f _{vco}	VCO operating fre	quency	48.0		100	MHz	
I _{pll}	PLL operating curi PLL @ 96 N 2 MHz, VDIV	rent IHz (f _{osc_hi_1} = 8 MHz, f _{pll_ref} = / multiplier = 48)	_	1060	_	μA	7
I _{pll}	PLL operating curi PLL @ 48 N 2 MHz, VDN	rent IHz (f _{osc_hi_1} = 8 MHz, f _{pll_ref} = V multiplier = 24)	_	600	_	μA	7
f _{pll_ref}	PLL reference free	quency range	2.0		4.0	MHz	
J _{cyc_pll}	PLL period jitter (F	RMS)					8
	• f _{vco} = 48 MH	Iz	_	120	_	ps	
	• f _{vco} = 100 M	Hz	_	50	_	ps	
J _{acc_pll}	PLL accumulated	jitter over 1µs (RMS)					8
	• f _{vco} = 48 MH	lz	_	1350	_	ps	
	• f _{vco} = 100 M	Hz	_	600	_	ps	
D _{lock}	Lock entry frequer	ncy tolerance	± 1.49	—	± 2.98	%	
D _{unl}	Lock exit frequence	y tolerance	± 4.47	—	± 5.97	%	

Table 15. MCG specifications (continued)

• 8 MHz (RANGE=01)

• 16 MHz

• 24 MHz

• 32 MHz

mode (HGO=0)

mode (HGO=1)

mode (HGO=0)

mode (HGO=1)

mode (HGO=0)

mode (HGO=0)

mode (HGO=1)

(HGO=1)

(HGO=0)

(HGO=1)

(HGO=0)

(HGO=1)

EXTAL load capacitance

XTAL load capacitance

Feedback resistor — low-frequency, low-power

Feedback resistor — low-frequency, high-gain

Feedback resistor — high-frequency, low-power

Feedback resistor — high-frequency, high-gain

Series resistor - low-frequency, high-gain mode

Series resistor - low-frequency, low-power

Series resistor - high-frequency, low-power

Series resistor — high-frequency, high-gain

Peak-to-peak amplitude of oscillation (oscillator

Peak-to-peak amplitude of oscillation (oscillator

Peak-to-peak amplitude of oscillation (oscillator

Peak-to-peak amplitude of oscillation (oscillator mode) — high-frequency, high-gain mode

mode) — high-frequency, low-power mode

mode) - low-frequency, low-power mode

mode) — low-frequency, high-gain mode

Cx

 C_v

 R_F

 R_S

V_{pp}⁵

Table 16. Oscillator DC electrical specifications (continued)							
Symbol	Description	Min.	Тур.	Max.	Unit	Notes	
IDDOSC	Supply current — high gain mode (HGO=1)					1	
	• 32 kHz	_	25	_	μA		
	• 4 MHz	_	400	_	μA		

500

2.5

3

4

10

1

200

0

0.6

V_{DD}

0.6

 V_{DD}

_

μA

mΑ

mΑ

mΑ

ΜΩ

MO

MΩ

MΩ

kΩ

kΩ

kΩ

kΩ

V

V

V

۷

2.3

2, 3

2, 4

1	$V_{DD}=3.3 V$	Temperature =25	°C
1.	v _{DD} -0.0 v,	Temperature –20	U

2. See crystal or resonator manufacturer's recommendation

- 3. C_x, C_y can be provided by using either the integrated capacitors or by using external components.
- 4. When low power mode is selected, R_F is integrated and must not be attached externally.
- 5. The EXTAL and XTAL pins should only be connected to required oscillator components and must not be connected to any other devices.

6.3.2.2 Oscillator frequency specifications Table 17. Oscillator frequency specifications

Symbol	Description	Min.	Тур.	Max.	Unit	Notes
f _{osc_lo}	Oscillator crystal or resonator frequency — low frequency mode (MCG_C2[RANGE]=00)	32	_	40	kHz	
f _{osc_hi_1}	Oscillator crystal or resonator frequency — high frequency mode (low range) (MCG_C2[RANGE]=01)	3	_	8	MHz	
f _{osc_hi_2}	Oscillator crystal or resonator frequency — high frequency mode (high range) (MCG_C2[RANGE]=1x)	8	_	32	MHz	
f _{ec_extal}	Input clock frequency (external clock mode)	—	—	50	MHz	1, 2
t _{dc_extal}	Input clock duty cycle (external clock mode)	40	50	60	%	
t _{cst}	Crystal startup time — 32 kHz low-frequency, low-power mode (HGO=0)	_	750	_	ms	3, 4
	Crystal startup time — 32 kHz low-frequency, high-gain mode (HGO=1)	_	250		ms	
	Crystal startup time — 8 MHz high-frequency (MCG_C2[RANGE]=01), low-power mode (HGO=0)	_	0.6	_	ms	•
	Crystal startup time — 8 MHz high-frequency (MCG_C2[RANGE]=01), high-gain mode (HGO=1)	_	1	_	ms	

1. Other frequency limits may apply when external clock is being used as a reference for the FLL or PLL.

2. When transitioning from FBE to FEI mode, restrict the frequency of the input clock so that, when it is divided by FRDIV, it remains within the limits of the DCO input clock frequency.

3. Proper PC board layout procedures must be followed to achieve specifications.

4. Crystal startup time is defined as the time between the oscillator being enabled and the OSCINIT bit in the MCG_S register being set.

NOTE

The 32 kHz oscillator works in low power mode by default and cannot be moved into high power/gain mode.

6.3.3 32 kHz Oscillator Electrical Characteristics

This section describes the module electrical characteristics.

6.3.3.1 32 kHz oscillator DC electrical specifications

Table 18. 32kHz oscillator DC electrical specifications

Symbol	Description	Min.	Тур.	Max.	Unit
V _{BAT}	Supply voltage	1.71	—	3.6	V
R _F	Internal feedback resistor	_	100	_	MΩ

Table continues on the next page ...



Figure 9. EzPort Timing Diagram

6.4.3 Flexbus Switching Specifications

All processor bus timings are synchronous; input setup/hold and output delay are given in respect to the rising edge of a reference clock, FB_CLK. The FB_CLK frequency may be the same as the internal system bus frequency or an integer divider of that frequency.

The following timing numbers indicate when data is latched or driven onto the external bus, relative to the Flexbus output clock (FB_CLK). All other timing relationships can be derived from these values.

Num	Description	Min.	Max.	Unit	Notes
	Operating voltage	2.7	3.6	V	
	Frequency of operation		FB_CLK	MHz	
FB1	Clock period	20	_	ns	
FB2	Address, data, and control output valid	_	11.5	ns	1
FB3	Address, data, and control output hold	0.5	_	ns	1
FB4	Data and FB_TA input setup	8.5	_	ns	2
FB5	Data and FB_TA input hold	0.5	—	ns	2

Table 25. Flexbus limited voltage range switching specifications

1. Specification is valid for all FB_AD[31:0], FB_BE/BWEn, FB_CSn, FB_OE, FB_R/W, FB_TBST, FB_TSIZ[1:0], FB_ALE, and FB_TS.





Figure 11. FlexBus write timing diagram

6.5 Security and integrity modules

There are no specifications necessary for the device's security and integrity modules.

6.6 Analog

6.6.1 ADC electrical specifications

The 16-bit accuracy specifications listed in Table 27 and Table 28 are achievable on the differential pins ADCx_DP0, ADCx_DM0, ADCx_DP1, ADCx_DM1, ADCx_DP3, and ADCx_DM3.

The ADCx_DP2 and ADCx_DM2 ADC inputs are connected to the PGA outputs and are not direct device pins. Accuracy specifications for these pins are defined in Table 29 and Table 30.

All other ADC channels meet the 13-bit differential/12-bit single-ended accuracy specifications.

Symbol	Description	Conditions	Min.	Typ. ¹	Max.	Unit	Notes
V _{DDA}	Supply voltage	Absolute	1.71	—	3.6	V	
ΔV_{DDA}	Supply voltage	Delta to V _{DD} (V _{DD} - V _{DDA})	-100	0	+100	mV	2
ΔV_{SSA}	Ground voltage	Delta to V _{SS} (V _{SS} - V _{SSA})	-100	0	+100	mV	2
V _{REFH}	ADC reference voltage high		1.13	V _{DDA}	V _{DDA}	V	
V _{REFL}	ADC reference voltage low		V _{SSA}	V _{SSA}	V _{SSA}	V	
V _{ADIN}	Input voltage	16-bit differential mode	VREFL	_	31/32 * VREFH	V	
		All other modes	VREFL	_	VREFH		
C _{ADIN}	Input capacitance	16-bit mode	—	8	10	pF	
		• 8-/10-/12-bit modes	_	4	5		
R _{ADIN}	Input resistance		—	2	5	kΩ	
R _{AS}	Analog source	13-/12-bit modes					3
	resistance	f _{ADCK} < 4 MHz	_	—	5	kΩ	
f _{ADCK}	ADC conversion clock frequency	≤ 13-bit mode	1.0		18.0	MHz	4
f _{ADCK}	ADC conversion clock frequency	16-bit mode	2.0		12.0	MHz	4
C _{rate}	ADC conversion	≤ 13 bit modes					5
	rate	No ADC hardware averaging	20.000	—	818.330	Ksps	
		Continuous conversions enabled, subsequent conversion time					

6.6.1.1 16-bit ADC operating conditions Table 27. 16-bit ADC operating conditions

Symbol	Description	Conditions ¹	Min.	Typ. ²	Max.	Unit	Notes
	ADC	• ADLPC = 1, ADHSC = 0	1.2	2.4	3.9	MHz	t _{ADACK} = 1/
	asynchronous clock source	• ADLPC = 1, ADHSC = 1	2.4	4.0	6.1	MHz	f _{ADACK}
f _{ADACK}		• ADLPC = 0, ADHSC = 0	3.0	5.2	7.3	MHz	
		• ADLPC = 0, ADHSC = 1	4.4	6.2	9.5	MHz	
	Sample Time	See Reference Manual chapter	for sample t	imes			
TUE	Total unadjusted	12-bit modes	_	±4	±6.8	LSB ⁴	5
	error	 <12-bit modes 	—	±1.4	±2.1		
DNL	Differential non-	12-bit modes		±0.7	-1.1 to +1.9	LSB ⁴	5
	linearity				-0.3 to 0.5		
		 <12-bit modes 	—	±0.2			
INL	Integral non-	12-bit modes	—	±1.0	-2.7 to +1.9	LSB ⁴	5
	linearity				-0.7 to +0.5		
		 <12-bit modes 		±0.5			
E _{FS}	Full-scale error	12-bit modes	—	-4	-5.4	LSB ⁴	V _{ADIN} =
		 <12-bit modes 	_	-1.4	-1.8		V _{DDA}
Eq	Quantization	16-bit modes		-1 to 0		LSB ⁴	
	error	 ≤13-bit modes 	—	_	±0.5		
ENOB	Effective number	16-bit differential mode					6
	of bits	• Avg = 32	12.8	14.5	—	bits	
		• Avg = 4	11.9	13.8	—	bits	
		16-bit single-ended mode					
		• Avg = 32	10.0	12.0		hita	
		• Avg = 4	12.2	10.1	_	Dits	
	Signal to poico		11.4	13.1		DIIS	
SINAD	plus distortion		6.02	2 × ENOB +	1.76	dB	
THD	Total harmonic	16-bit differential mode					7
	distortion	• Avg = 32	—	-94	—	dB	
		16-bit single-ended mode		05		-10	
		• Avg = 32	_	-85	_	dВ	
SFDR	Spurious free	16-bit differential mode					7
	dynamic range	• Avg = 32	82	95	—	dB	
		16-bit single-ended mode					
		• Avg = 32	/8	90		aВ	
		-					

Table 28. 1	16-bit ADC characteristics	$(V_{REFH} = V_{DDA})$	$V_{\text{REFL}} = V$	V _{SSA}) (continued))
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Symbol	Description	Conditions ¹	Min.	Typ. ²	Max.	Unit	Notes
E _{IL}	Input leakage error		I _{In} × R _{AS}			mV	I _{In} = leakage current (refer to the MCU's voltage and current operating ratings)
	Temp sensor slope	Across the full temperature range of the device		1.715	_	mV/°C	
V _{TEMP25}	Temp sensor voltage	25 °C	_	719	—	mV	

Table 28. 16-bit ADC characteristics ($V_{REFH} = V_{DDA}$, $V_{REFL} = V_{SSA}$) (continued)

- 1. All accuracy numbers assume the ADC is calibrated with V_{REFH} = V_{DDA}
- Typical values assume V_{DDA} = 3.0 V, Temp = 25°C, f_{ADCK} = 2.0 MHz unless otherwise stated. Typical values are for reference only and are not tested in production.
- The ADC supply current depends on the ADC conversion clock speed, conversion rate and the ADLPC bit (low power). For lowest power operation the ADLPC bit must be set, the HSC bit must be clear with 1 MHz ADC conversion clock speed.
- 4. 1 LSB = $(V_{REFH} V_{REFL})/2^N$
- 5. ADC conversion clock < 16 MHz, Max hardware averaging (AVGE = %1, AVGS = %11)
- 6. Input data is 100 Hz sine wave. ADC conversion clock < 12 MHz.
- 7. Input data is 1 kHz sine wave. ADC conversion clock < 12 MHz.







Symbol	Description	Conditions	Min.	Typ. ¹	Max.	Unit	Notes
C _{rate}	ADC conversion	≤ 13 bit modes	18.484	_	450	Ksps	7
	rate	No ADC hardware averaging					
		Continuous conversions enabled					
		Peripheral clock = 50 MHz					
		16 bit modes	37.037		250	Ksps	8
		No ADC hardware averaging					
		Continuous conversions enabled					
		Peripheral clock = 50 MHz					

Table 29. 16-bit ADC with PGA operating conditions (continued)

- 1. Typical values assume V_{DDA} = 3.0 V, Temp = 25°C, f_{ADCK} = 6 MHz unless otherwise stated. Typical values are for reference only and are not tested in production.
- 2. ADC must be configured to use the internal voltage reference (VREF_OUT)
- 3. PGA reference is internally connected to the VREF_OUT pin. If the user wishes to drive VREF_OUT with a voltage other than the output of the VREF module, the VREF module must be disabled.
- 4. For single ended configurations the input impedance of the driven input is R_{PGAD}/2
- 5. The analog source resistance (R_{AS}), external to MCU, should be kept as minimum as possible. Increased R_{AS} causes drop in PGA gain without affecting other performances. This is not dependent on ADC clock frequency.
- The minimum sampling time is dependent on input signal frequency and ADC mode of operation. A minimum of 1.25µs time should be allowed for F_{in}=4 kHz at 16-bit differential mode. Recommended ADC setting is: ADLSMP=1, ADLSTS=2 at 8 MHz ADC clock.
- 7. ADC clock = 18 MHz, ADLSMP = 1, ADLST = 00, ADHSC = 1
- 8. ADC clock = 12 MHz, ADLSMP = 1, ADLST = 01, ADHSC = 1

6.6.1.4 16-bit ADC with PGA characteristics with Chop enabled (ADC_PGA[PGACHPb] =0) Table 30. 16-bit ADC with PGA characteristics

Symbol	Description	Conditions	Min.	Typ. ¹	Max.	Unit	Notes
I _{DDA_PGA}	Supply current	Low power (ADC_PGA[PGALPb]=0)	_	420	644	μA	2
I _{DC_PGA}	Input DC current		$\frac{2}{R_{\rm PGAD}} \left(\frac{(V_{\rm REFPGA} \times 0.583) - V_{\rm CM}}{({\rm Gain}+1)} \right)$			A	3
		Gain =1, V_{REFPGA} =1.2V, V_{CM} =0.5V	_	1.54	_	μA	
		Gain =64, V_{REFPGA} =1.2V, V_{CM} =0.1V	_	0.57	—	μA	

Symbol	Description	Min.	Тур.	Max.	Unit	Notes
C _{REF}	Internal reference capacitor	—	1	—	pF	
V _{DELTA}	Oscillator delta voltage	—	500	_	mV	2, 5
I _{REF}	Reference oscillator current source base current • 2 μA setting (REFCHRG = 0)	_	2	3	μA	2, 6
	 32 µA setting (REFCHRG = 15) 		36	50		
I _{ELE}	Electrode oscillator current source base current • 2 µA setting (EXTCHRG = 0)	_	2	3	μA	2, 7
	• 32 µA setting (EXTCHRG = 15)		36	50		
Pres5	Electrode capacitance measurement precision	—	8.3333	38400	fF/count	8
Pres20	Electrode capacitance measurement precision	_	8.3333	38400	fF/count	9
Pres100	Electrode capacitance measurement precision	—	8.3333	38400	fF/count	10
MaxSens	Maximum sensitivity	0.008	1.46	_	fF/count	11
Res	Resolution	_	_	16	bits	
T _{Con20}	Response time @ 20 pF	8	15	25	μs	12
I _{TSI_RUN}	Current added in run mode	_	55		μA	
I _{TSI_LP}	Low power mode current adder		1.3	2.5	μA	13

Table 49. TSI electrical specifications (continued)

1. The TSI module is functional with capacitance values outside this range. However, optimal performance is not guaranteed.

2. Fixed external capacitance of 20 pF.

- 3. REFCHRG = 2, EXTCHRG=0.
- 4. REFCHRG = 0, EXTCHRG = 10.

5. $V_{DD} = 3.0 V.$

- 6. The programmable current source value is generated by multiplying the SCANC[REFCHRG] value and the base current.
- 7. The programmable current source value is generated by multiplying the SCANC[EXTCHRG] value and the base current.
- 8. Measured with a 5 pF electrode, reference oscillator frequency of 10 MHz, PS = 128, NSCN = 8; lext = 16.
- 9. Measured with a 20 pF electrode, reference oscillator frequency of 10 MHz, PS = 128, NSCN = 2; lext = 16.
- 10. Measured with a 20 pF electrode, reference oscillator frequency of 10 MHz, PS = 16, NSCN = 3; lext = 16.
- 11. Sensitivity defines the minimum capacitance change when a single count from the TSI module changes. Sensitivity depends on the configuration used. The documented values are provided as examples calculated for a specific configuration of operating conditions using the following equation: (C_{ref} * I_{ext})/(I_{ref} * PS * NSCN)

The typical value is calculated with the following configuration:

 $I_{ext} = 6 \ \mu A \ (EXTCHRG = 2), PS = 128, NSCN = 2, I_{ref} = 16 \ \mu A \ (REFCHRG = 7), C_{ref} = 1.0 \ pF$

The minimum value is calculated with the following configuration:

 $I_{ext} = 2 \ \mu A$ (EXTCHRG = 0), PS = 128, NSCN = 32, $I_{ref} = 32 \ \mu A$ (REFCHRG = 15), $C_{ref} = 0.5 \ pF$

The highest possible sensitivity is the minimum value because it represents the smallest possible capacitance that can be measured by a single count.

- 12. Time to do one complete measurement of the electrode. Sensitivity resolution of 0.0133 pF, PS = 0, NSCN = 0, 1 electrode, EXTCHRG = 7.
- 13. REFCHRG=0, EXTCHRG=4, PS=7, NSCN=0F, LPSCNITV=F, LPO is selected (1 kHz), and fixed external capacitance of 20 pF. Data is captured with an average of 7 periods window.

7 Dimensions

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